Dual 2-input NAND gate

Rev. 3 — 27 March 2013

### 1. General description

The 74AHC2G00; 74AHCT2G00 are high-speed Si-gate CMOS devices. They provide two 2-input NAND gates.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

### 2. Features and benefits

- Symmetrical output impedance
- High noise immunity
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101C exceeds 1000 V
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

### 3. Ordering information

#### Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC2G00DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body	SOT505-2
74AHCT2G00DP			width 3 mm; lead length 0.5 mm	
74AHC2G00DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads;	SOT765-1
74AHCT2G00DC			body width 2.3 mm	
74AHC2G00GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads;	SOT996-2
74AHCT2G00GD			8 terminals; body $3 \times 2 \times 0.5$ mm	



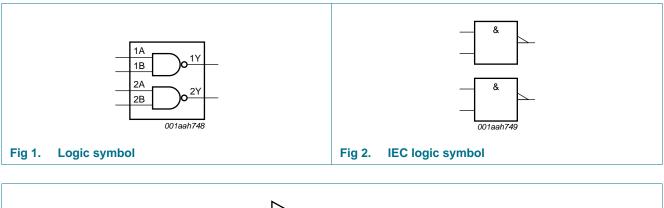
**Dual 2-input NAND gate** 

### 4. Marking

Table 2. Marking	
Type number	Marking code <sup>[1]</sup>
74AHC2G00DP	A00
74AHCT2G00DP	C00
74AHC2G00DC	A00
74AHCT2G00DC	C00
74AHC2G00GD	A00
74AHCT2G00GD	C00

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

## 5. Functional diagram



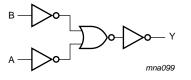
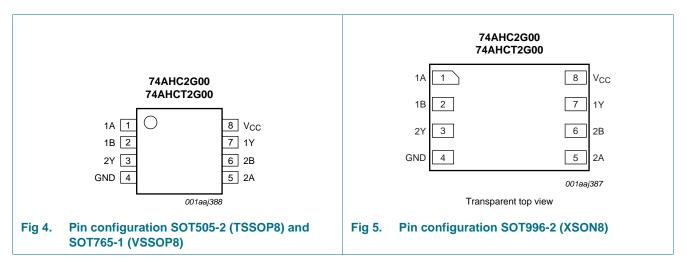


Fig 3. Logic diagram (one gate)

**Dual 2-input NAND gate** 

## 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V <sub>CC</sub>	8	supply voltage

## 7. Functional description

Table 4.	Function table <sup>[1]</sup>		
Input			Output
nA		nB	nY
L		L	н
L		Н	Н
Н		L	Н
Н		Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

				.0	,
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
l <sub>IK</sub>	input clamping current	V <sub>I</sub> < -0.5 V	<u>[1]</u> –20	-	mA
I <sub>ОК</sub>	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> -	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I <sub>CC</sub>	supply current		-	75	mA
I <sub>GND</sub>	ground current		-75	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$	[2] _	250	mW
1 101	total power alcolpation			200	

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K. For XSON8 package: above 45 °C the value of P<sub>tot</sub> derates linearly with 2.4 mW/K.

### 9. Recommended operating conditions

#### Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74	4AHC2G	00	74	AHCT20	600	Unit
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	$V_{CC}$ = 3.3 V $\pm$ 0.3 V	-	-	100	-	-	-	ns/V
	and fall rate	$V_{CC}=5.0~V\pm0.5~V$	-	-	20	-	-	20	ns/V

## **10. Static characteristics**

#### Table 7.Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	ol Parameter Conditions			25 °C		–40 °C t	o +85 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHC2	G00									
V <sub>IH</sub>	HIGH-level	$V_{CC} = 2.0 V$	1.5	-	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 3.0 V$	2.1	-	-	2.1	-	2.1	-	V
		V <sub>CC</sub> = 5.5 V	3.85	-	-	3.85	-	3.85	-	V

74AHC\_AHCT2G00

Product data sheet

© NXP B.V. 2013. All rights reserved.

Dual 2-input NAND gate

Voltages	are referenced	to GND (ground = 0 V).								
Symbol	Parameter	Conditions		25 °C		–40 °C t	to +85 °C	-40 °C 1	to +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
VIL	LOW-level	$V_{CC} = 2.0 V$	-	-	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 3.0 V$	-	-	0.9	-	0.9	-	0.9	V
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V <sub>OH</sub>	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_{O}$ = -50 $\mu$ A; $V_{CC}$ = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		$I_{O}$ = –50 $\mu\text{A};V_{CC}$ = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		$I_{O}$ = –50 $\mu\text{A};V_{CC}$ = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O}$ = -8.0 mA; $V_{CC}$ = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_{O}$ = 50 $\mu A; V_{CC}$ = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \ \mu\text{A}; \ V_{CC} = 3.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \ \mu\text{A}; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O}$ = 4.0 mA; $V_{CC}$ = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		$I_{O}$ = 8.0 mA; $V_{CC}$ = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I <sub>I</sub>	input leakage current	$V_1 = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μΑ
I <sub>CC</sub>	supply current		-	-	10	-	10	-	40	μΑ
CI	input capacitance		-	1.5	10	-	10	-	10	pF
74AHCT	2G00									
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level	$V_{I}$ = $V_{IH}$ or $V_{IL};V_{CC}$ = 4.5 V								
	output voltage	I <sub>O</sub> = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I <sub>CC</sub>	supply current		-	-	1.0	-	10	-	40	μΑ
$\Delta I_{CC}$	additional supply current	per input pin; $V_I = 3.4 V$ ; other inputs at $V_{CC}$ or GND; $I_O = 0 A$ ; $V_{CC} = 5.5 V$	-	-	1.35	-	1.5	-	1.5	mA
CI	input capacitance		-	1.5	10	-	10	-	10	pF

## Table 7. Static characteristics ...continued Voltages are referenced to GND (ground = 0.01)

**Dual 2-input NAND gate** 

## **11. Dynamic characteristics**

#### Table 8. Dynamic characteristics

GND = 0 V; for test circuit see Figure 7.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	–40 °C t	to +125 °C	Unit
			-	Min	Тур	Max	Min	Max	Min	Max	
74AHC2	G00							I			
t <sub>pd</sub>	propagation	nA, nB to nY; see Figure 6	[1]								
	delay	$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	[2]								
		C <sub>L</sub> = 15 pF		-	4.5	7.9	1.0	9.5	1.0	10.5	ns
		C <sub>L</sub> = 50 pF		-	6.5	11.4	1.0	13.0	1.0	14.5	ns
		$V_{CC}$ = 4.5 V to 5.5 V	[3]								
		C <sub>L</sub> = 15 pF		-	3.5	5.5	1.0	6.5	1.0	7.0	ns
		C <sub>L</sub> = 50 pF		-	4.9	7.5	1.0	8.5	1.0	9.5	ns
C <sub>PD</sub>	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}; f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	17	-	-	-	-	-	pF
74AHCT	2G00										
t <sub>pd</sub>	propagation	nA, nB to nY; see Figure 6	[1]								
	delay	$V_{CC}$ = 4.5 V to 5.5 V	[3]								
		C <sub>L</sub> = 15 pF		1.0	3.6	6.2	1.0	7.1	1.0	8.0	ns
		C <sub>L</sub> = 50 pF		1.0	5.0	7.9	1.0	9.0	1.0	10.0	ns
C <sub>PD</sub>	power dissipation capacitance	per buffer; C <sub>L</sub> = 50 pF; $f_i$ = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub>	<u>[4]</u>	-	18	-	-	-	-	-	pF

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[2] Typical values are measured at  $V_{CC}$  = 3.3 V.

[3] Typical values are measured at  $V_{CC} = 5.0$  V.

[4]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu$ W).  $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$  where:  $f_i$  = input frequency in MHz;  $f_o$  = output frequency in MHz;  $C_L$  = output load capacitance in pF;

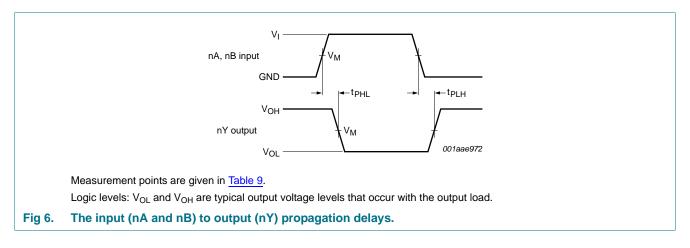
 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$  = sum of the outputs.

**Dual 2-input NAND gate** 

## 12. Waveforms



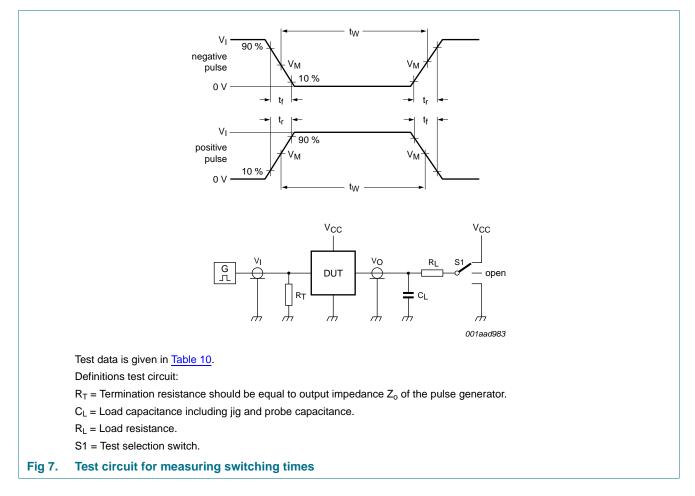
#### Table 9.Measurement points

Туре	Input	Output
	V <sub>M</sub>	V <sub>M</sub>
74AHC2G00	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>
74AHCT2G00	1.5 V	0.5V <sub>CC</sub>

### **NXP Semiconductors**

# 74AHC2G00; 74AHCT2G00

### Dual 2-input NAND gate

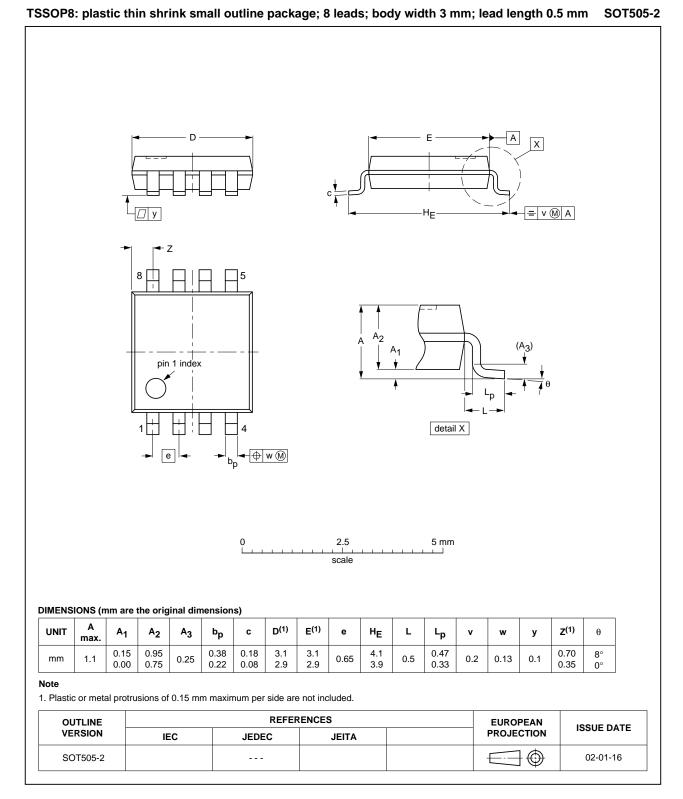


#### Table 10. Test data

Туре	Input		Load	S1 position	
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	RL	t <sub>PHL</sub> , t <sub>PLH</sub>
74AHC2G00	V <sub>CC</sub>	≤ 3 ns	15 pF, 50 pF	1 kΩ	open
74AHCT2G00	3 V	$\leq$ 3 ns	15 pF, 50 pF	1 kΩ	open

**Dual 2-input NAND gate** 

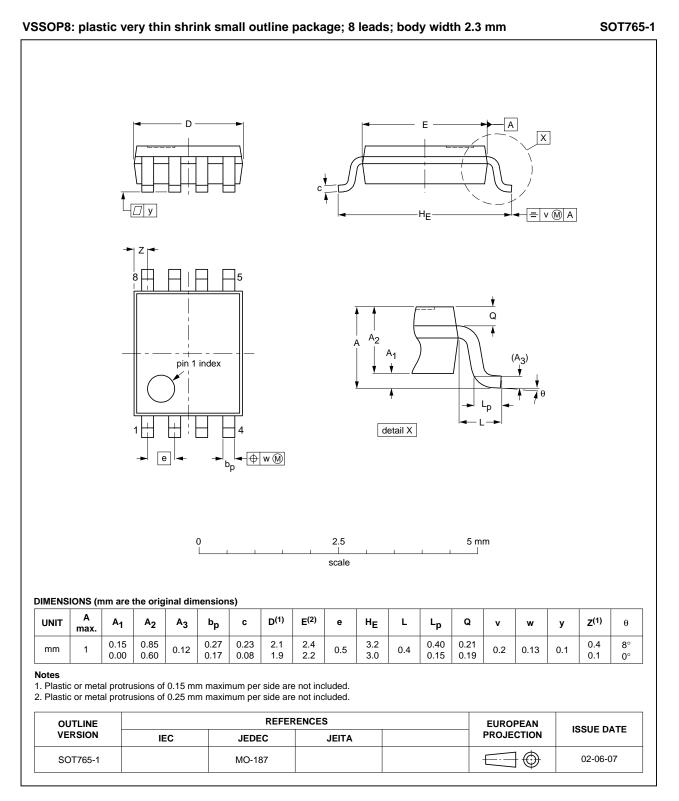
## 13. Package outline



#### Fig 8. Package outline SOT505-2 (TSSOP8)

All information provided in this document is subject to legal disclaimers.

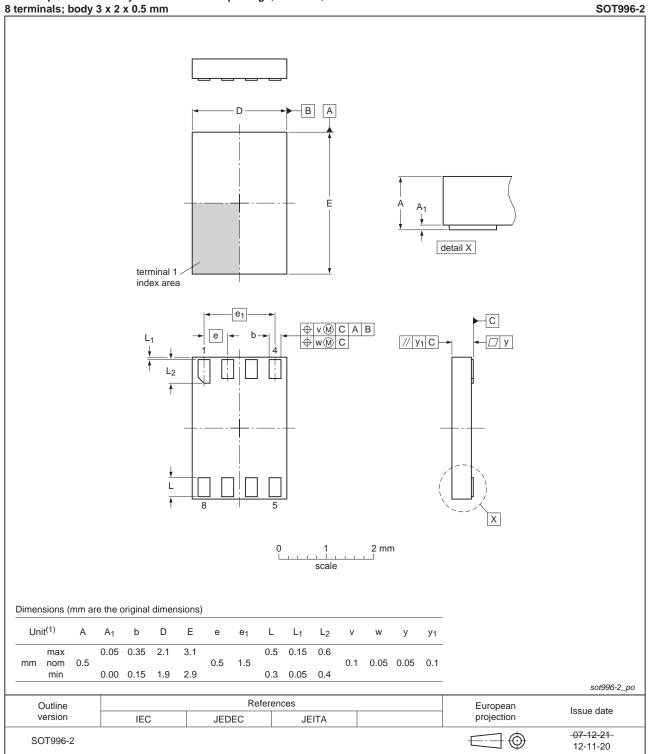
**Dual 2-input NAND gate** 



#### Fig 9. Package outline SOT765-1 (VSSOP8)

All information provided in this document is subject to legal disclaimers.

**Dual 2-input NAND gate** 



XSON8: plastic extremely thin small outline package; no leads; 8 terminals: body 3 x 2 x 0.5 mm

Fig 10. Package outline SOT996-2 (XSON8)

All information provided in this document is subject to legal disclaimers.

Dual 2-input NAND gate

## 14. Abbreviations

Acronym CDM CMOS	Description Charged Device Model Complementary Metal-Oxide Semiconductor
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## **15. Revision history**

#### Table 12.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT2G00 v.3	20130327	Product data sheet	-	74AHC_AHCT2G00 v.2
Modifications:	<ul> <li>For type numbers 74AHC2G00GD and 74AHCT2G00GD XSON8U has changed to XSON8.</li> </ul>			
74AHC_AHCT2G00 v.2	20090112	Product data sheet	-	74AHC_AHCT2G00 v.1
74AHC_AHCT2G00 v.1	20040101	Product specification	-	-

## **16. Legal information**

### 16.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

#### 16.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

### 16.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof. Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nxp.com/profile/terms">http://www.nxp.com/profile/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

74AHC\_AHCT2G00

© NXP B.V. 2013. All rights reserved.

#### **Dual 2-input NAND gate**

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

**Non-automotive qualified products** — Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond

NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

**Translations** — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

### 16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

## 17. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

**Dual 2-input NAND gate** 

### **18. Contents**

1	General description 1
2	Features and benefits 1
3	Ordering information 1
4	Marking 2
5	Functional diagram 2
6	Pinning information 3
6.1	Pinning 3
6.2	Pin description 3
7	Functional description 3
8	Limiting values 4
9	Recommended operating conditions 4
10	Static characteristics 4
11	Dynamic characteristics 6
12	Waveforms
13	Package outline 9
14	Abbreviations 12
15	Revision history 12
16	Legal information
16.1	Data sheet status 13
16.2	Definitions 13
16.3	Disclaimers
16.4	Trademarks 14
17	Contact information 14
18	Contents 15

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2013.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 27 March 2013 Document identifier: 74AHC\_AHCT2G00